



N-Channel 30-V (D-S) MOSFET

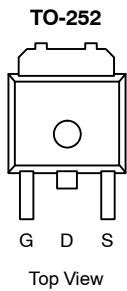
PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a
30	0.016 @ V _{GS} = 10 V	15
	0.024 @ V _{GS} = 4.5 V	12

FEATURES

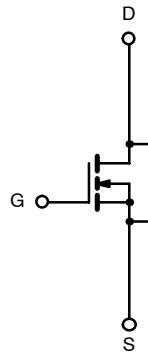
- TrenchFET® Power MOSFET
- PWM Optimized
- 100% R_g Tested

APPLICATIONS

- High-Side DC/DC
 - Desktop
 - Server
- DDR DC/DC Converter



Drain Connected to Tab



N-Channel MOSFET

Ordering Information: SUD50N03-16P—E3 (Lead Free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	±20	
Continuous Drain Current ^a	T _C = 25 °C	I _D	37	A
	T _A = 25 °C		15	
	T _A = 100 °C		10.6	
Pulsed Drain Current		I _{DM}	40	
Continuous Source Current (Diode Conduction) ^a		I _S	5	
Avalanche Current		I _{AS}	25	mJ
Single Pulse Avalanche Energy		E _{AS}	31.25	
Maximum Power Dissipation	T _C = 25 °C	P _D	40.8	W
	T _A = 25 °C		6.5 ^a	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	18	23	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R _{thJC}	3.0	3.7	

Notes

a. Surface Mounted on FR4 Board, t ≤ 10 sec.

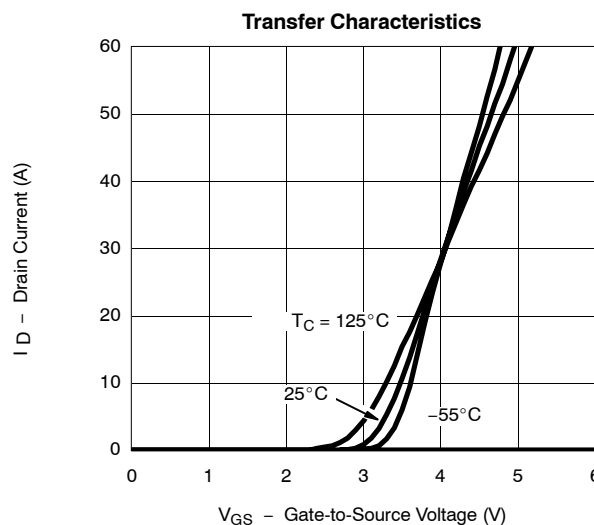
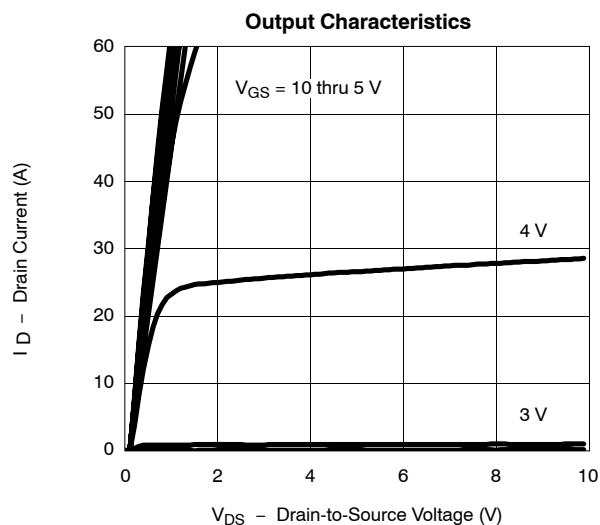
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 125°C			50	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	40			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 15 A		0.0128	0.016	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125°C			0.025	
		V _{GS} = 4.5 V, I _D = 10 A		0.019	0.024	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A	10			S
Dynamic^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		1150		pF
Output Capacitance	C _{oss}			215		
Reverse Transfer Capacitance	C _{rss}			70		
Total Gate Charge ^c	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 50 A		8.5	13	nC
Gate-Source Charge ^c	Q _{gs}			5		
Gate-Drain Charge ^c	Q _{gd}			2.5		
Gate Resistance	R _g			2.7	5.5	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 0.3 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 2.5 Ω		7	15	ns
Rise Time ^c	t _r			20	30	
Turn-Off Delay Time ^c	t _{d(off)}			25	40	
Fall Time ^c	t _f			12	20	
Source-Drain Diode Ratings and Characteristic (T_C = 25°C)						
Pulsed Current	I _{SM}				40	A
Diode Forward Voltage ^b	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1.0	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 40 A, di/dt = 100 A/μs		25	70	ns

Notes

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- c. Independent of operating temperature.

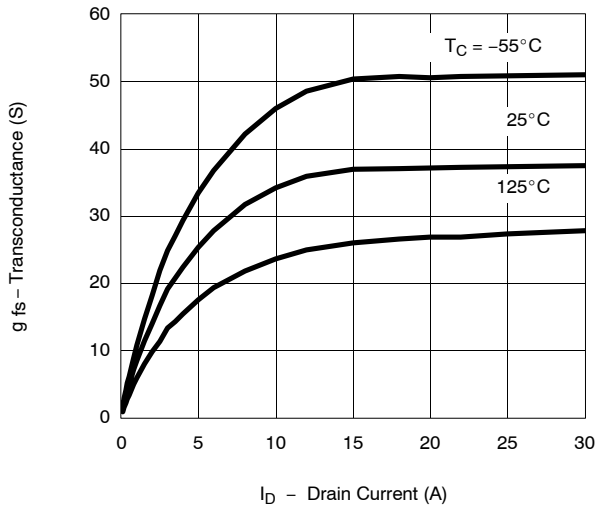
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



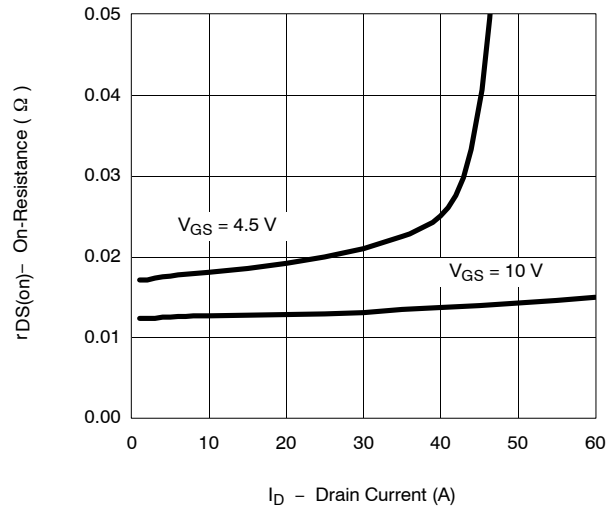


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

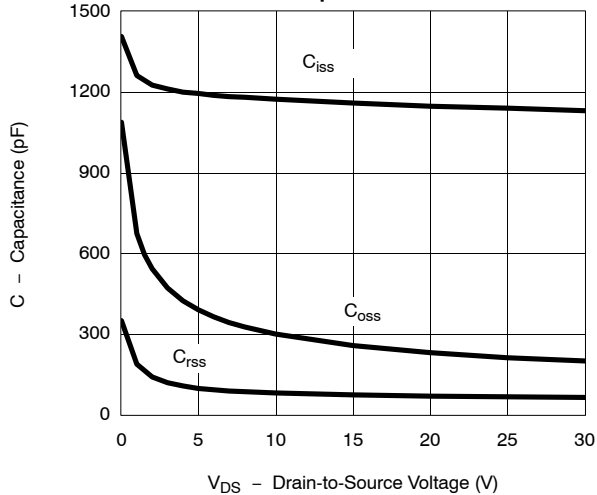
Transconductance



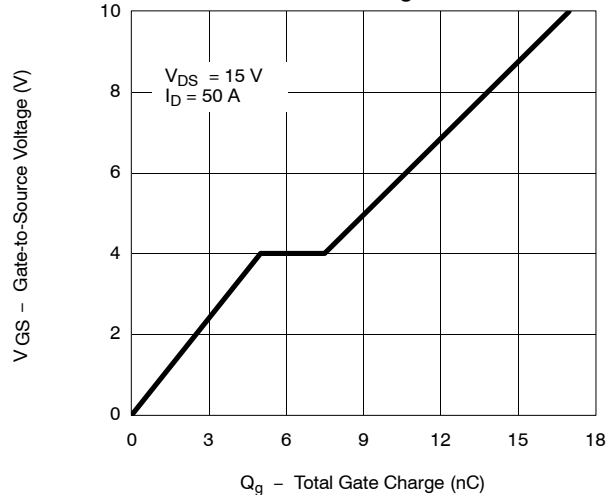
On-Resistance vs. Drain Current



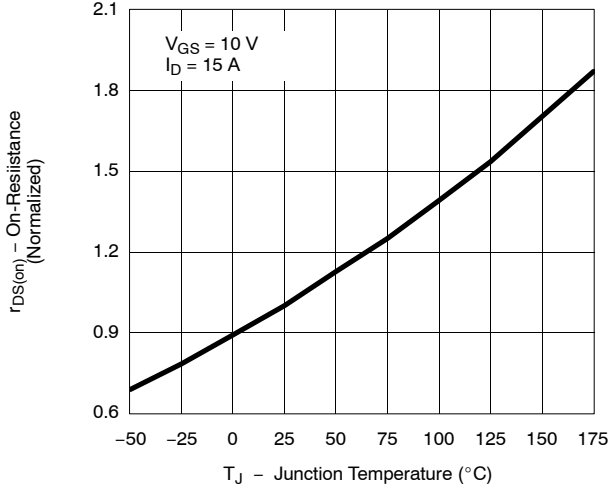
Capacitance



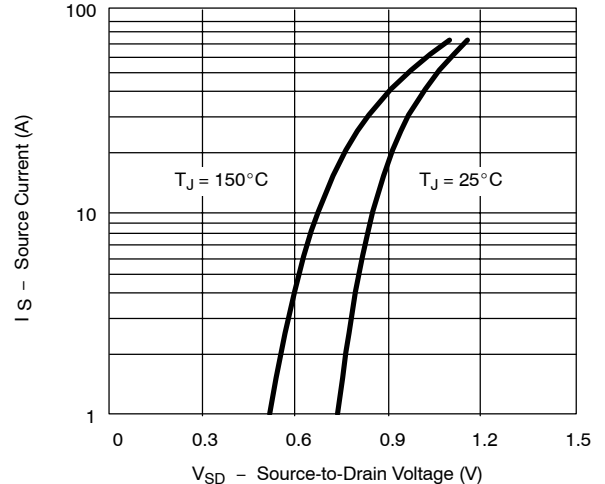
Gate Charge



On-Resistance vs. Junction Temperature

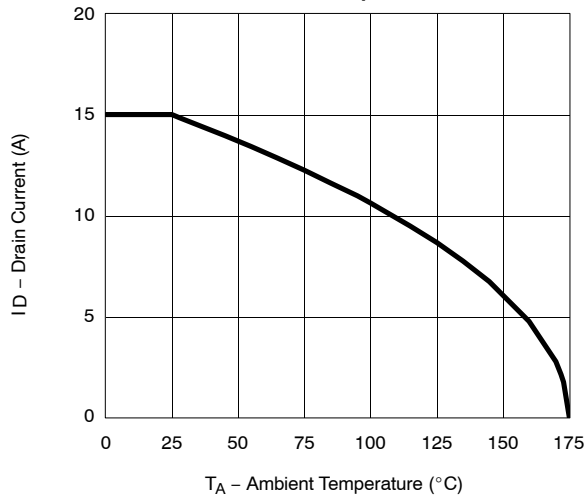


Source-Drain Diode Forward Voltage

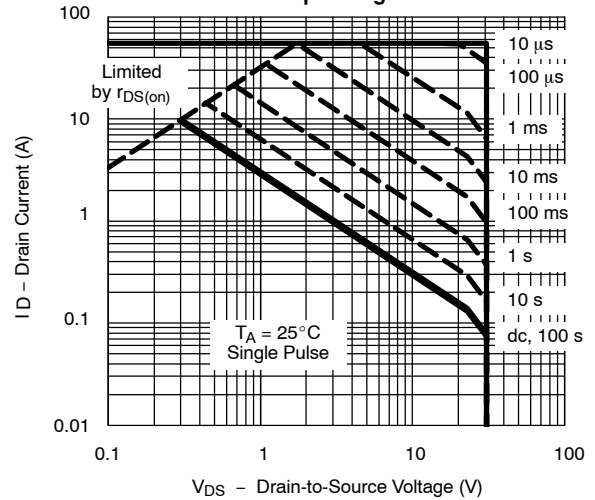


THERMAL RATINGS

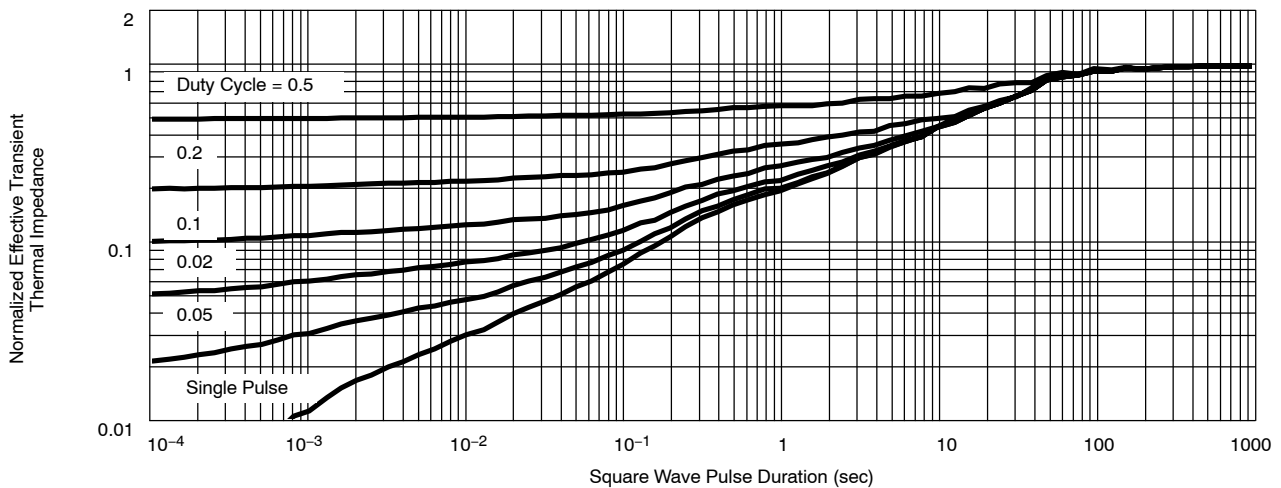
Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

